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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/709,846	06/01/2004	Ching-Huei Tsai	NAUP0572USA	3845
27765	7590 10/18/2005		EXAMINER	
NORTH AMERICA INTELLECTUAL PROPERTY CORPORATION			HU, SHOUXIANG	
P.O. BOX 506 MERRIFIELD, VA 22116		ART UNIT	PAPER NUMBER	
			2811	
		DATE MAILED: 10/18/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

V ord R EX

	Application No.	Applicant(s)	
	10/709,846	TSAI, CHING-HUEI	
Office Action Summary	Examiner	Art Unit	
	Shouxiang Hu	2811	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DATE of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period was a failure to reply within the set or extended period for reply will, by statute any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be time will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).	
Status			
 1) ☐ Responsive to communication(s) filed on 2a) ☐ This action is FINAL. 2b) ☑ This 3) ☐ Since this application is in condition for alloward closed in accordance with the practice under Expression in the practice of the	action is non-final. nce except for formal matters, pro		
Disposition of Claims			
 4) ☐ Claim(s) 1-16 is/are pending in the application 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-16 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or 	wn from consideration.		
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomplicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine 10.	epted or b) objected to by the lead of both drawing (s) be held in abeyance. See tion is required if the drawing (s) is objected to by the lead of the drawing (s) is objected to by the lead of the drawing (s) is objected to by the lead of the lea	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Application in the second	on No ed in this National Stage	
Attachment/c)			
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date S. Patent and Trademark Office	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	-	

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 1. Claims 1-9 and 11-16 are rejected under 35 U.S.C. 102(b) as being anticipated by Applicant's admitted prior art ("AAPA").

AAPA discloses a semiconductor wafer and/or capacitor (Figs. 1-5), comprising: a silicon substrate with first, second and third regions on the substrate surface, wherein the three regions can be defined as illustrated in the attached drawing (Attachment A) and they are all on (i.e., near and/or above) the surface of the substrate; a field oxide (14); and, a capacitor on the substrate, including: a first electrode (16; polysilicon) in the first and third regions; a first isolation layer (18); and, a second electrode (22; polysilicon) in the second and third regions; a second isolation layer (26), a first contact plug (28); and, a second contact plug (32).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and

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the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claim 10 is rejected under 35 U.S.C. 103(a) as being unpatentable over AAPA.

The disclosure of AAPA is discussed as applied to claims 1-9 and 11-16 above.

Although AAPA does not expressly disclose that the first insulation layer can be formed of silicon oxide or silicon nitride, it is noted that it is art known that each of the two materials are commonly used in the art for forming a gate dielectric layer and/or a capacitor dielectric layer for good insulation performance with desired compatible depositing process.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to make the device of AAPA with the first insulation layer being formed of the art-known commonly-used insulating material of silicon oxide or silicon nitride, so that a semiconductor device with good internal insulation performance and/or with desired compatible depositing process would be obtained.

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. References A-D are cited as being related to a capacitor structure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shouxiang Hu whose telephone number is 571-272-1654. The examiner can normally be reached on Monday through Thursday, 7:30 AM to 6:00 PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

SH

October 13, 2005

SHOUXIANG HU PRIMARY EXAMINER

Attachment: Attachment A

Attachment A: 25

Fig. 1 Prior art